

L Number	Hits	Search Text	DB	Time stamp
3	12	(("4,688,078") or ("4,939,559") or ("5,474,947") or ("5,488,612") or ("5,959,465") or ("6,009,011") or ("6,317,364") or ("6,341,084") or ("6,377,070") or ("6,514,842") or ("6,730,575") or ("6,754,108")).PN.	USPAT; US-PGPUB	2004/11/07 17:10
4	0	(lead adj oxide with dielectric) with floating adj gate	USPAT; US-PGPUB	2004/11/07 17:13
5	1	(lead adj oxide with dielectric) and floating adj gate	USPAT; US-PGPUB	2004/11/07 17:13
6	0	work adj function near3 silicon adj dioxide and @pd>20040521	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/11/07 17:14
7	6	((("4271487") or ("4333166") or ("4760556") or ("5042011") or ("5111427") or ("5153853") or ("5280205") or ("5399516") or ("5418739") or ("5424569") or ("5488587") or ("5497494") or ("5619642") or ("5627785") or ("5796670") or ("5801401") or ("5852306") or ("5870327") or ("5880991") or ("5986932") or ("6009011")).PN.) and sram	USPAT	2004/11/07 17:14
8	10	(((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric and @pd>20040521	USPAT; US-PGPUB	2004/11/07 17:14
9	0	tunnel adj barrier near3 silicon adj dioxide and @pd>20040521	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/11/07 17:14
10	10	(((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric and @pd>20040521	USPAT; US-PGPUB	2004/11/07 17:14
11	2	perovskite near3 gate and @pd>20040521	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:15
12	4	((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate) and @pd>20040521	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:15
13	87	(US-6501677-\$ or US-6501692-\$ or US-6504765-\$ or US-6504775-\$ or US-6504786-\$ or US-6504788-\$ or US-6507124-\$ or US-6509616-\$ or US-6510075-\$ or US-6510076-\$ or US-6528817-\$ or US-6528839-\$ or US-6529397-\$ or US-6529399-\$ or US-6529401-\$ or US-6529403-\$ or US-6529407-\$ or US-6529408-\$ or US-6531731-\$ or US-6532169-\$ or US-6534819-\$ or US-6535417-\$ or US-6535442-\$ or US-6535453-\$ or US-6538277-\$ or US-6538338-\$).did. or (US-6542401-\$ or US-6545297-\$ or US-6545311-\$ or US-6545905-\$ or US-6549448-\$ or US-6549449-\$ or US-6549450-\$ or US-6549451-\$ or US-6549452-\$ or US-6549453-\$ or US-6549458-\$ or US-6512245-\$ or US-6512691-\$ or US-6512700-\$ or US-6512718-\$ or US-6515894-\$ or US-6515931-\$ or US-6519176-\$ or US-6519204-\$ or US-6522569-\$ or US-6522582-\$ or US-6522586-\$ or US-6525382-\$ or US-6525962-\$ or US-6525983-\$ or US-6525985-\$ or US-6493255-\$).did. or (US-6493256-\$ or US-6493267-\$ or US-6496887-\$ or US-6501127-\$).did. or (US-20020179960-\$ or US-20020179964-\$ or US-20020180069-\$ or US-20020181273-\$ or US-20020181274-\$ or US-20020185692-\$ or US-20020186579-\$ or US-20020186580-\$ or US-20020186581-\$ or US-20020190343-\$ or US-20020191436-\$ or US-20020195669-\$ or US-20030002328-\$ or US-20030007380-\$ or US-20030007381-\$ or US-20030012049-\$ or US-20030016554-\$ or US-20030021144-\$ or US-20030026124-\$ or US-20030026150-\$ or US-20030038317-\$ or US-20030042553-\$ or US-20030043538-\$ or US-20030043618-\$ or US-20030052371-\$ or US-20030053330-\$).did. or (US-20030058687-\$ or US-20030063485-\$ or US-20030063490-\$ or US-20030067043-\$).did.	USPAT; US-PGPUB	2004/11/07 17:15
14	4	((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate) and @pd>20040521	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:15
15	177	(sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20040521)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/11/07 17:15
16	10	(channel adj hot) and (tantalum titanium zirconium niobium) adj oxide and @pd>20040521	USPAT; US-PGPUB	2004/11/07 17:15

17	4	((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate) and @pd>20040521	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:15
18	7	(channel adj hot) and tantalum adj oxide and aluminum adj oxide and @pd>20040521	USPAT;	2004/11/07 17:16
19	446	aluminum adj oxide with dielectric and @pd>20040521	USPAT; US-PGPUB	2004/11/07 17:16
20	1	("6,210,999").PN.) and (al. sub aluminum)	USPAT; US-PGPUB	2004/11/07 17:16
21	446	aluminum adj oxide with dielectric and @pd>20040521	USPAT; US-PGPUB	2004/11/07 17:16
22	138	(channel adj hot adj electron) and oxide and @pd>20040521	USPAT; US-PGPUB	2004/11/07 17:16
23	17	(tunnel adj barrier barrier adj height) near3 silicon and @pd>20040521	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/07 17:17
24	1	("62033392" "6,210,999").PN. and (al. sub aluminum)	USPAT; US-PGPUB	2004/11/07 17:17
25	4	("6,122,191") or ("5,892,712") or ("6141248") and @pd>20040521	USPAT; US-PGPUB	2004/11/07 17:18
26	70	((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate and @pd>20040521	USPAT; US-PGPUB	2004/11/07 17:18
27	712	(257/314,315,316,317,321,324,390,410,411,903,904 or 365/149,154,185.01,185.08).CCLS. and @pd>20040521	USPAT; US-PGPUB	2004/11/07 17:18
28	1153	sram and @pd>20040521 not dram	USPAT; US-PGPUB	2004/11/07 17:19